

isc N-Channel MOSFET Transistor IRF200P223, IIRF200P223

• FEATURES

- Static drain-source on-resistance:
 $R_{DS(on)} \leq 11.5m\Omega$
- Enhancement mode:
 $V_{th} = 2.0$ to 4.0 V ($V_{DS}=V_{GS}$, $I_D=270 \mu$ A)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• DESCRIPTION

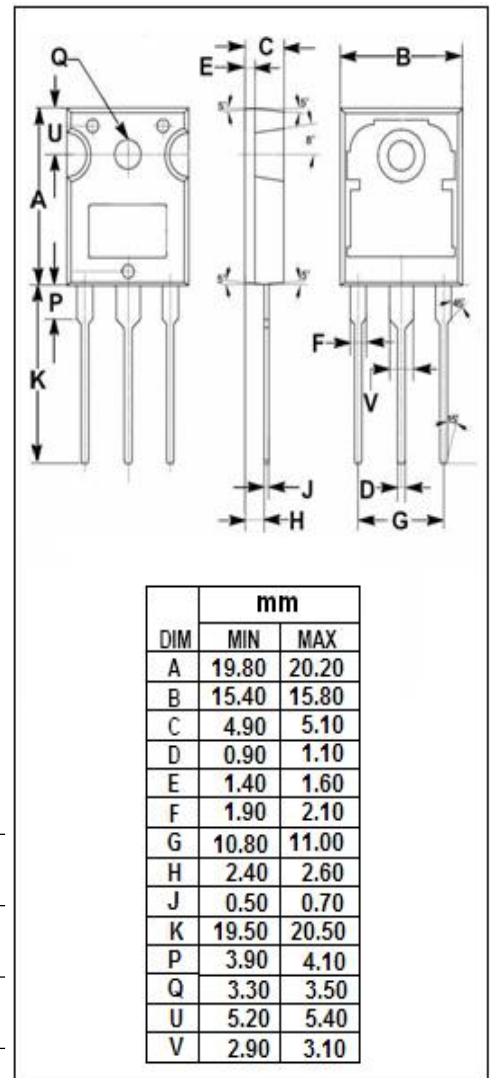
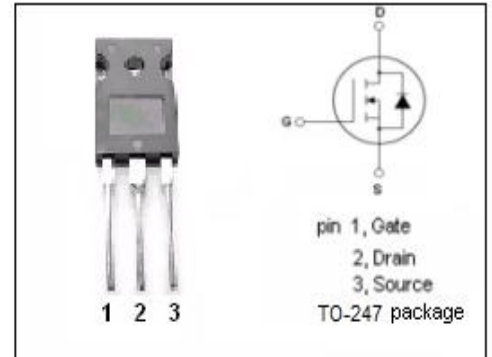
- OR-ring and redundant power switches

• ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DS}	Drain-Source Voltage	200	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-Continuous	100	A
I_{DM}	Drain Current-Single Pulsed	400	A
P_D	Total Dissipation @ $T_c=25^\circ C$	313	W
T_j	Max. Operating Junction Temperature	175	$^\circ C$
T_{stg}	Storage Temperature	-55~175	$^\circ C$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(j-c)}$	Channel-to-case thermal resistance	0.48	$^\circ C/W$
$R_{th(j-a)}$	Channel-to-ambient thermal resistance	40	$^\circ C/W$



isc N-Channel MOSFET Transistor IRF200P223, IIRF200P223**ELECTRICAL CHARACTERISTICS**T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D =1mA	200			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} ; I _D =270 μA	2.0		4.0	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =60A			11.5	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} = 20V			0.1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =160V; V _{GS} = 0V			1.0	μA
V _{SD}	Diode forward voltage	I _S =60A, V _{GS} = 0V			1.2	V

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